



# STF10N62K3, STF110N62K3, STI10N62K3, STP10N62K3

N-channel 620 V, 0.68  $\Omega$  typ., 8.4 A SuperMESH3™  
Power MOSFET in TO-220FP, I<sup>2</sup>PAKFP, I<sup>2</sup>PAK, TO-220 packages

Datasheet – production data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>	P <sub>w</sub>
STF10N62K3	620 V	< 0.75 $\Omega$	8.4 A <sup>(1)</sup>	30 W
STF110N62K3				
STI10N62K3			8.4 A	125 W
STP10N62K3				

1. Limited by package

- 100% avalanche tested
- Extremely high dv/dt capability
- Gate charge minimized
- Very low intrinsic capacitances
- Improved diode reverse recovery characteristics
- Zener-protected

## Applications

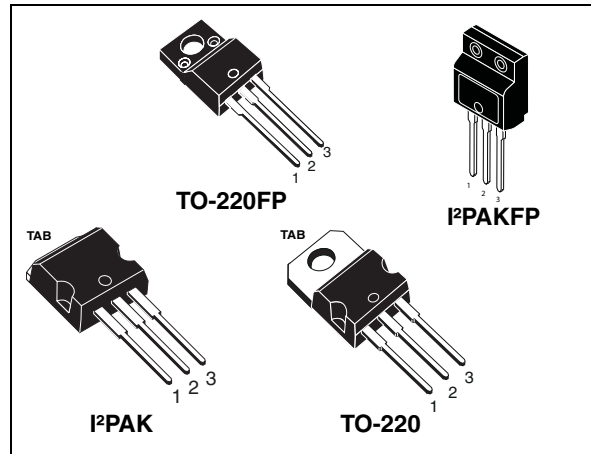
- Switching applications

## Description

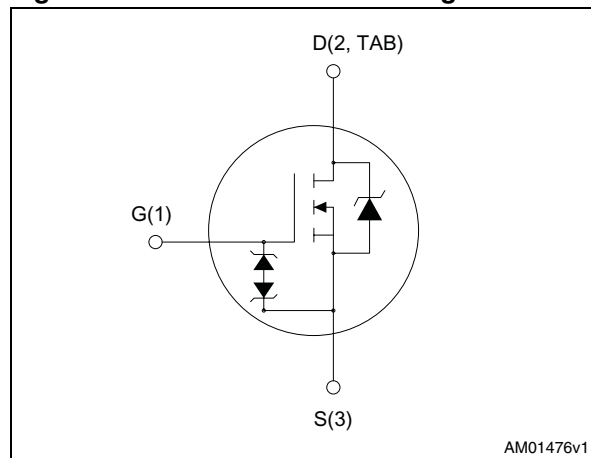
These SuperMESH3™ Power MOSFETs are the result of improvements applied to STMicroelectronics' SuperMESH™ technology, combined with a new optimized vertical structure. These devices boast an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering them suitable for the most demanding applications.

**Table 1. Device summary**

Order codes	Marking	Package	Packaging
STF10N62K3	10N62K3	TO-220FP	Tube
STF110N62K3	10N62K3	I <sup>2</sup> PAKFP	
STI10N62K3	10N62K3	I <sup>2</sup> PAK	
STP10N62K3	10N62K3	TO-220	



**Figure 1. Internal schematic diagram**



# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220FP I <sup>2</sup> PAKFP	I <sup>2</sup> PAK TO-220	
V <sub>DS</sub>	Drain source voltage	620		V
V <sub>GS</sub>	Gate-source voltage	± 30		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	8.4 <sup>(1)</sup>	8.4	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	5.2 <sup>(1)</sup>	5.2	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	33.6 <sup>(1)</sup>	33.6	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	30	125	W
I <sub>AR</sub>	Max current during repetitive or single pulse avalanche (pulse width limited by T <sub>JMAX</sub> )	8		A
E <sub>AS</sub>	Single pulse avalanche energy <sup>(3)</sup>	220		mJ
dv/dt <sup>(4)</sup>	Peak diode recovery voltage slope	12		V/ns
ESD	Gate-source human body model (R = 1.5 kΩ, C = 100 pF)	2.5		kV
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T <sub>C</sub> =25 °C)	2500		V
T <sub>j</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to 150		°C

1. Limited by maximum junction temperature

2. Pulse width limited by safe operating area

3. Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = I<sub>AR</sub>, V<sub>DD</sub> = 50 V

4. I<sub>SD</sub> ≤ 8.4 A, di/dt = 400 A/μs, V<sub>DD</sub> = 80% V<sub>(BR)DSS</sub>, V<sub>DS peak</sub> ≤ V<sub>(BR)DSS</sub>

**Table 3. Thermal data**

Symbol	Parameter	Value		Unit
		TO-220FP I <sup>2</sup> PAKFP	I <sup>2</sup> PAK TO-220	
R <sub>thj-case</sub>	Thermal resistance junction-case max	4.17	1.00	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	62.5		°C/W

## 2 Electrical characteristics

(T<sub>case</sub> = 25 °C unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	620			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = 620 V V <sub>DS</sub> = 620 V, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±10	μA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 100 μA	3	3.75	4.5	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A		0.68	0.75	Ω

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4 A	-	6	-	S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>DS</sub> = 50 V, f = 1 MHz, V <sub>GS</sub> = 0	-	1250 138 16	-	pF pF pF
C <sub>o(tr)</sub> <sup>(2)</sup>	Equivalent capacitance time related	V <sub>DS</sub> = 0 to 496 V, V <sub>GS</sub> = 0	-	56	-	pF
C <sub>o(er)</sub> <sup>(3)</sup>	Equivalent capacitance energy related	V <sub>DS</sub> = 0 to 496 V, V <sub>GS</sub> = 0	-	38	-	pF
R <sub>G</sub>	Gate input resistance	f = 1 MHz Gate DC Bias = 0 Test signal level = 20 mV open drain	-	3.5	-	Ω
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	V <sub>DD</sub> = 496 V, I <sub>D</sub> = 8 A, V <sub>GS</sub> = 10 V (see <a href="#">Figure 18</a> )	-	42 7.4 23	-	nC nC nC

1. Pulsed: pulse duration = 300 μs, duty cycle 1.5%
2. C<sub>oss eq</sub> time related is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>
3. C<sub>oss eq</sub> energy related is defined as a constant equivalent capacitance giving the same stored energy as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 310\text{ V}$ , $I_D = 4\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 17</a> )	-	14.5	-	ns
$t_r$	Rise time			15		ns
$t_{d(off)}$	Turn-off-delay time			41		ns
$t_f$	Fall time			31		ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		8.4	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				33.6	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 8\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 22</a> )	-	320		ns
$Q_{rr}$	Reverse recovery charge			2		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			13		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 22</a> )	-	410		ns
$Q_{rr}$	Reverse recovery charge			2.9		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			14		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage ( $I_D = 0$ )	$I_{GS} = \pm 1\text{ mA}$	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220FP, I<sup>2</sup>PAKFP

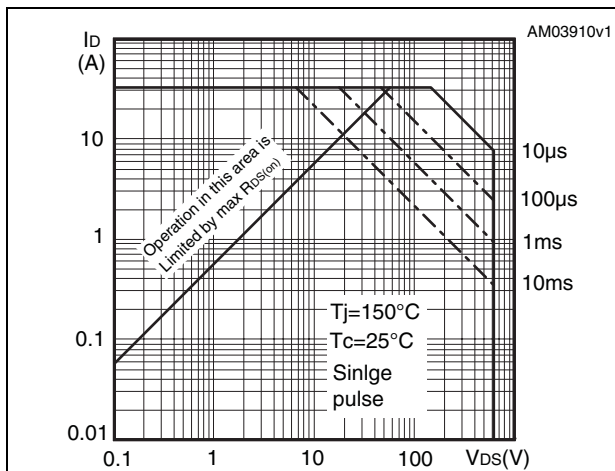


Figure 3. Thermal impedance for TO-220FP, I<sup>2</sup>PAKFP

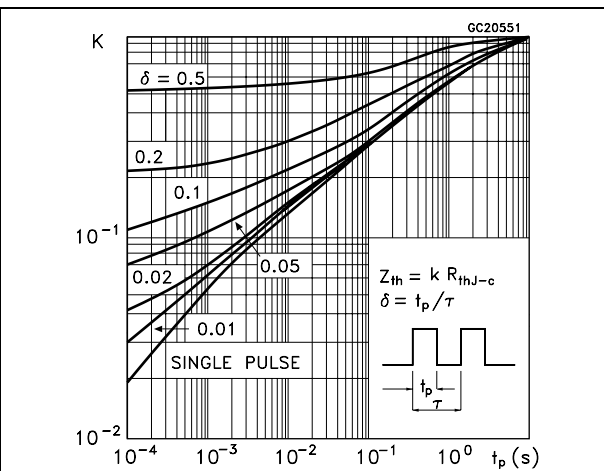


Figure 4. Safe operating area for I<sup>2</sup>PAK, TO-220

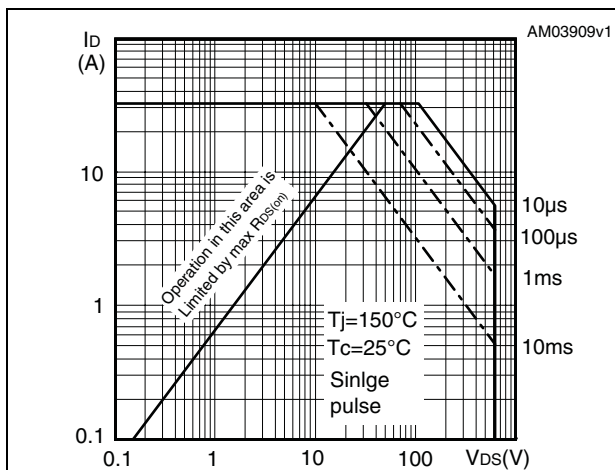


Figure 5. Thermal impedance for I<sup>2</sup>PAK, TO-220

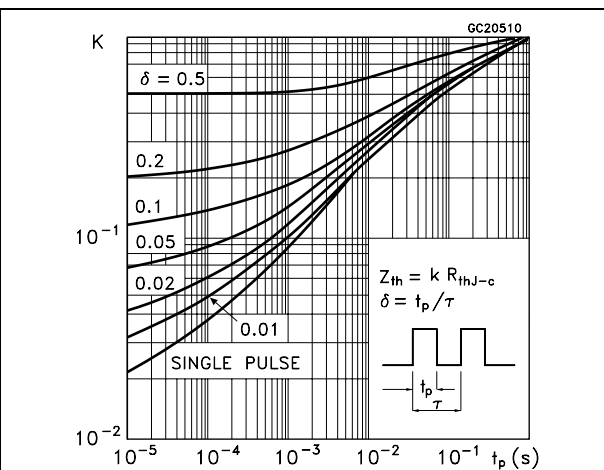


Figure 6. Output characteristics

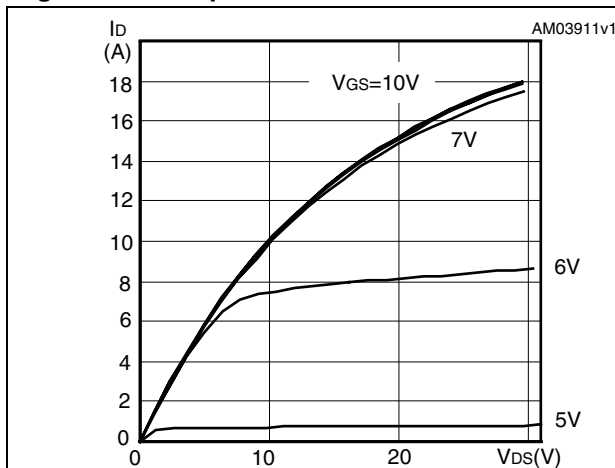


Figure 7. Transfer characteristics

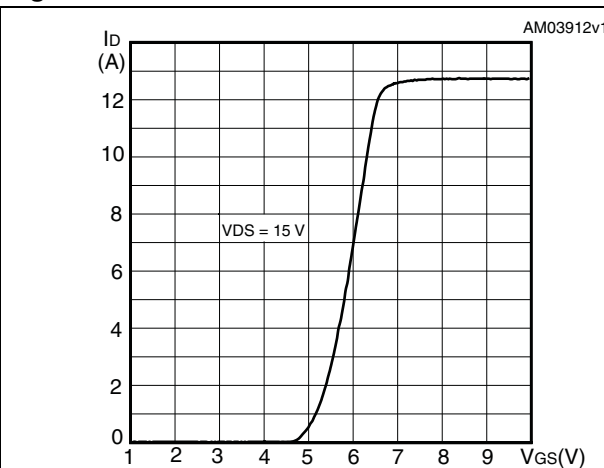


Figure 8. Normalized  $BV_{DSS}$  vs temperature

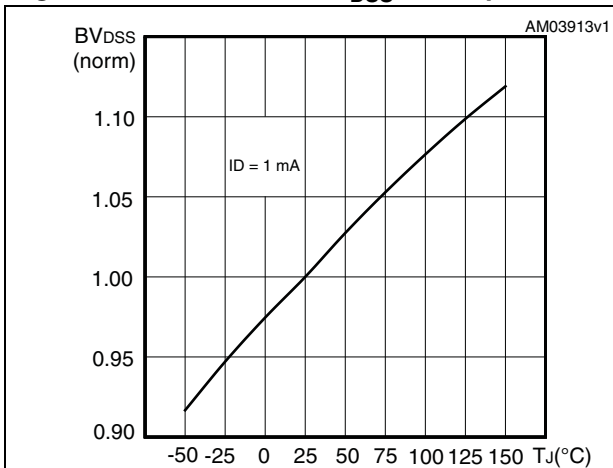


Figure 9. Static drain-source on-resistance

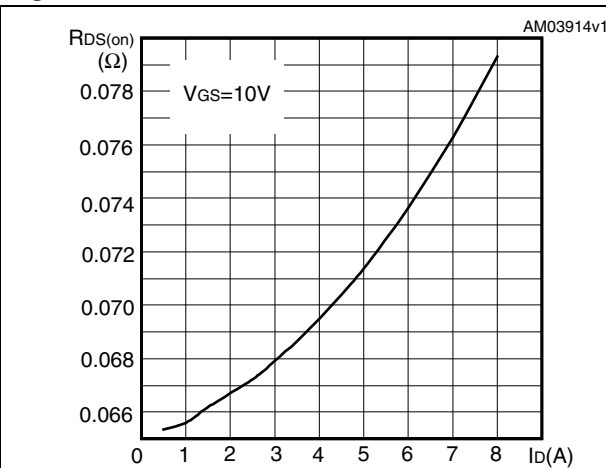


Figure 10. Output capacitance stored energy

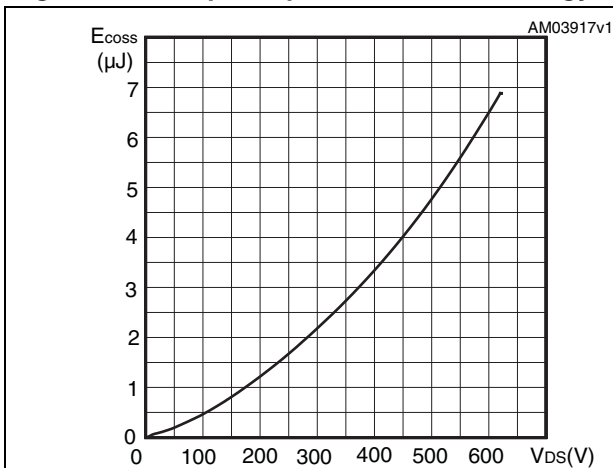


Figure 11. Capacitance variations

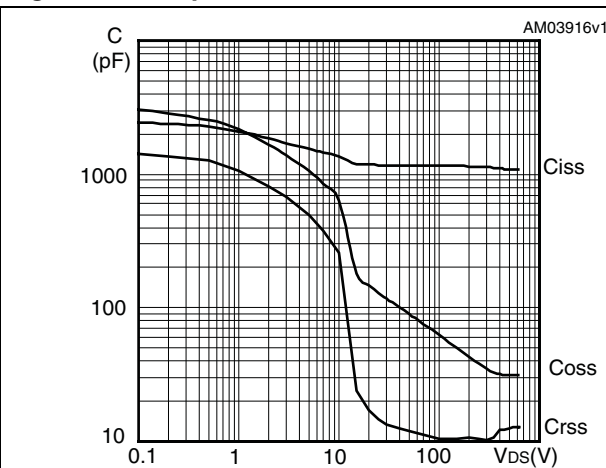


Figure 12. Gate charge vs gate-source voltage

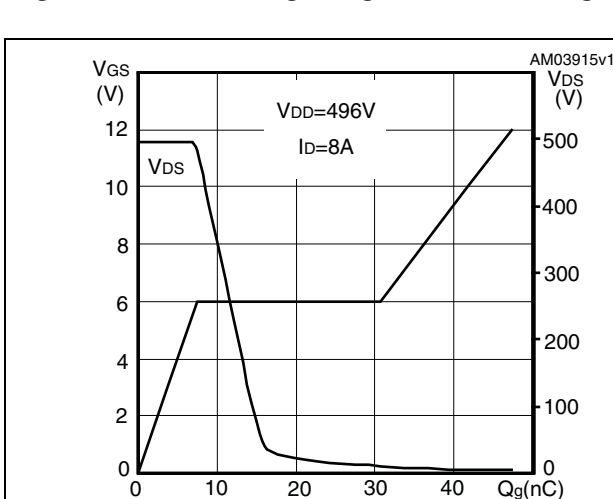


Figure 13. Normalized on-resistance vs temperature

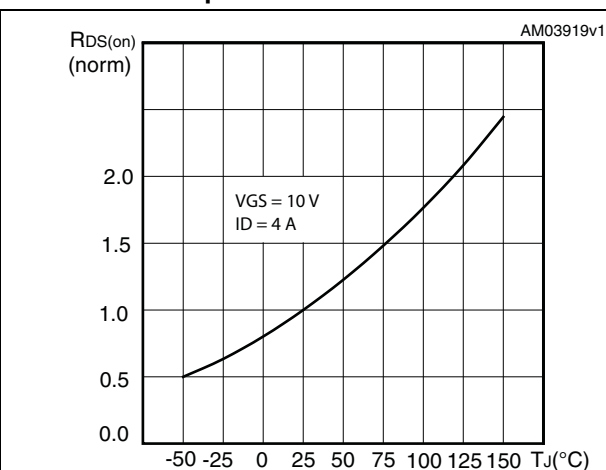


Figure 14. Normalized gate threshold voltage vs temperature

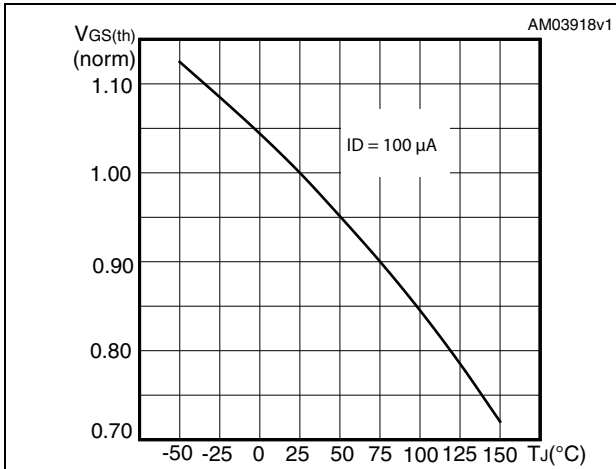


Figure 15. Maximum avalanche energy vs temperature

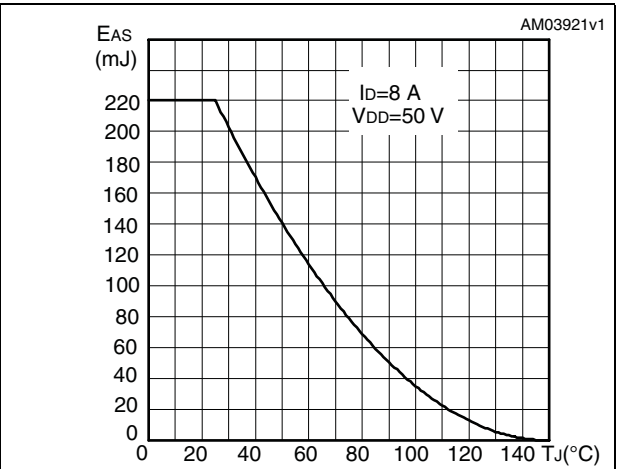
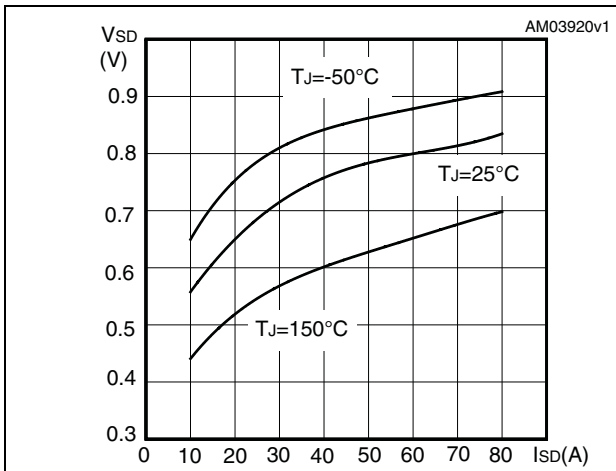


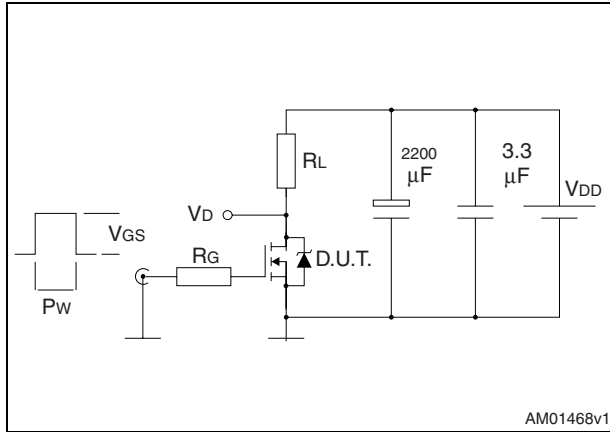
Figure 16. Source-drain diode forward characteristics



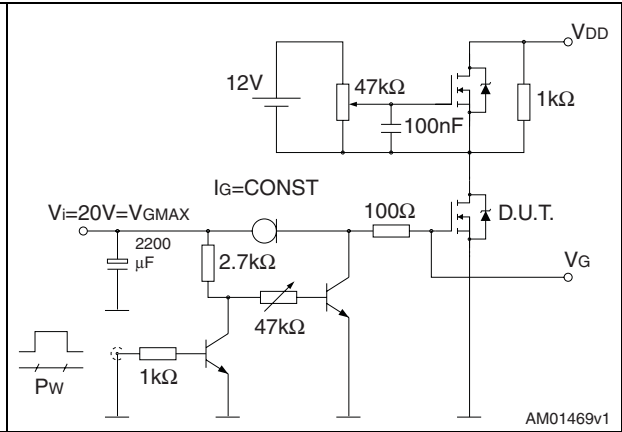


### 3 Test circuits

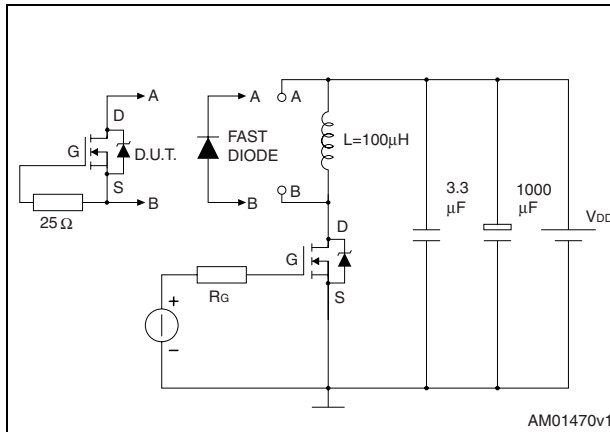
**Figure 17. Switching times test circuit for resistive load**



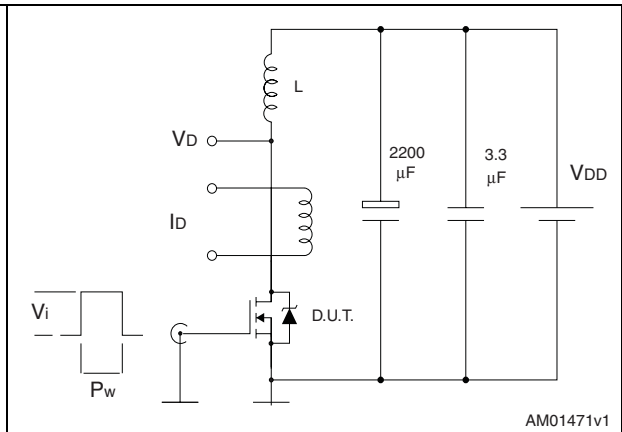
**Figure 18. Gate charge test circuit**



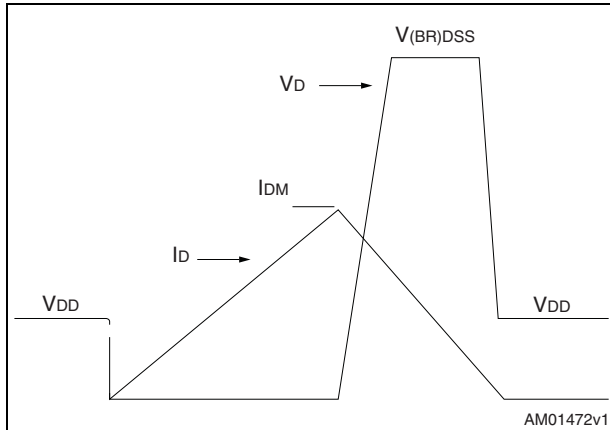
**Figure 19. Test circuit for inductive load switching and diode recovery times**



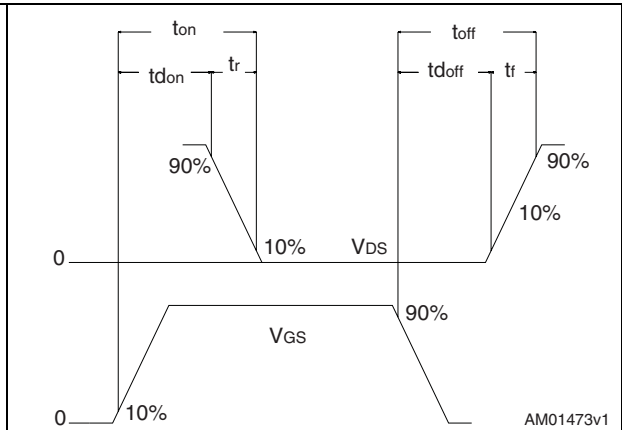
**Figure 20. Unclamped inductive load test circuit**



**Figure 21. Unclamped inductive waveform**



**Figure 22. Switching time waveform**



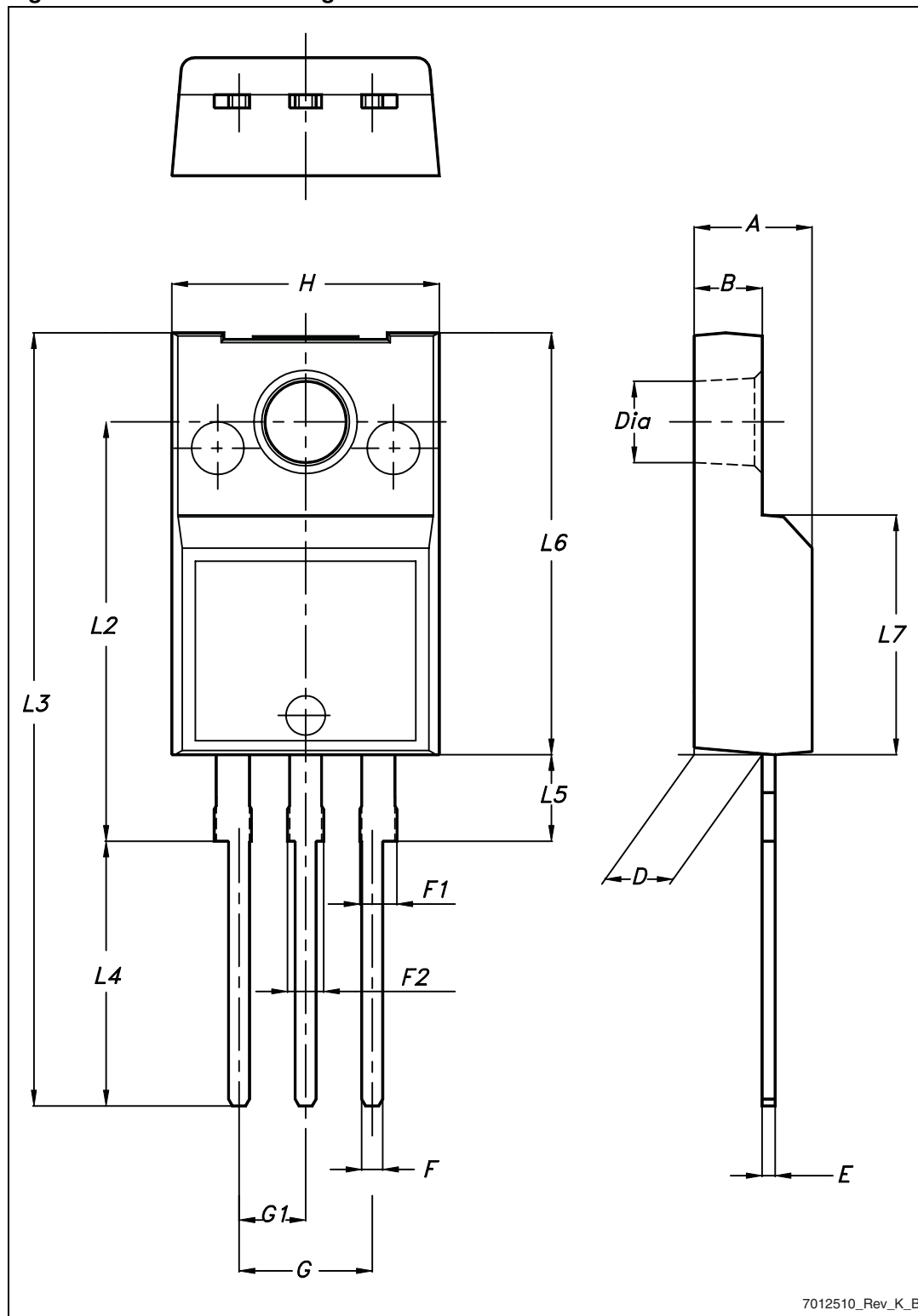
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 9. TO-220FP mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 23. TO-220FP drawing

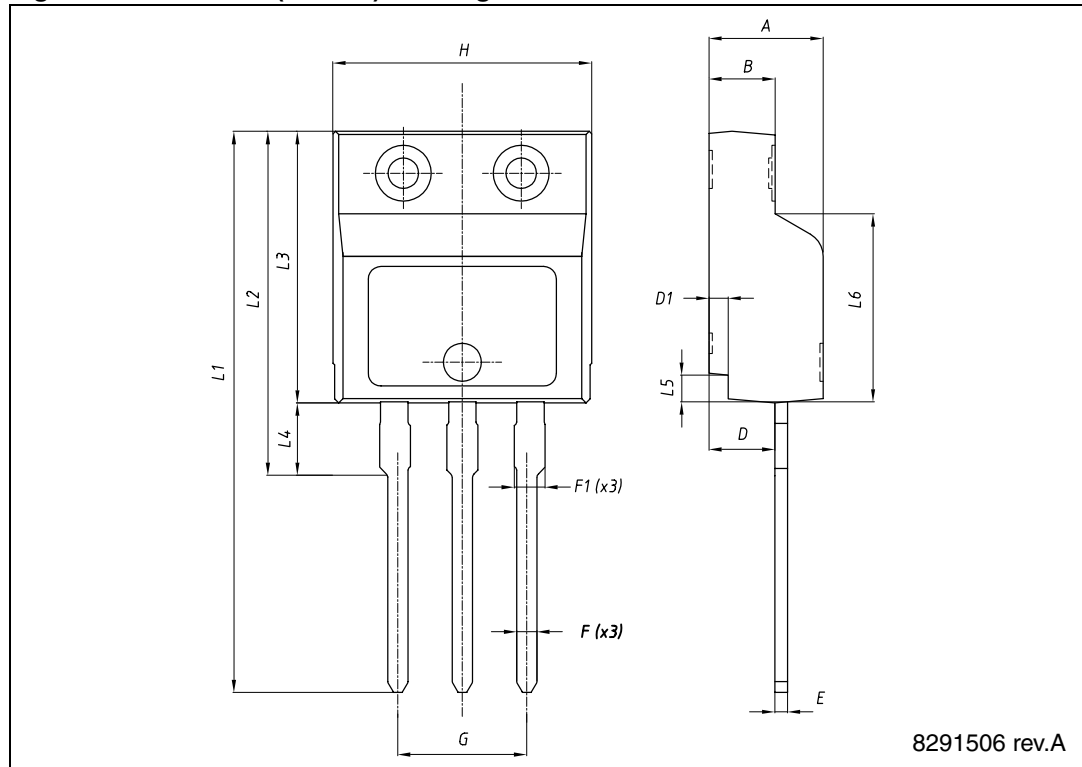


7012510\_Rev\_K\_B

Table 10. I<sup>2</sup>PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

Figure 24. I<sup>2</sup>PAKFP (TO-281) drawing



8291506 rev.A

Table 11. I<sup>2</sup>PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

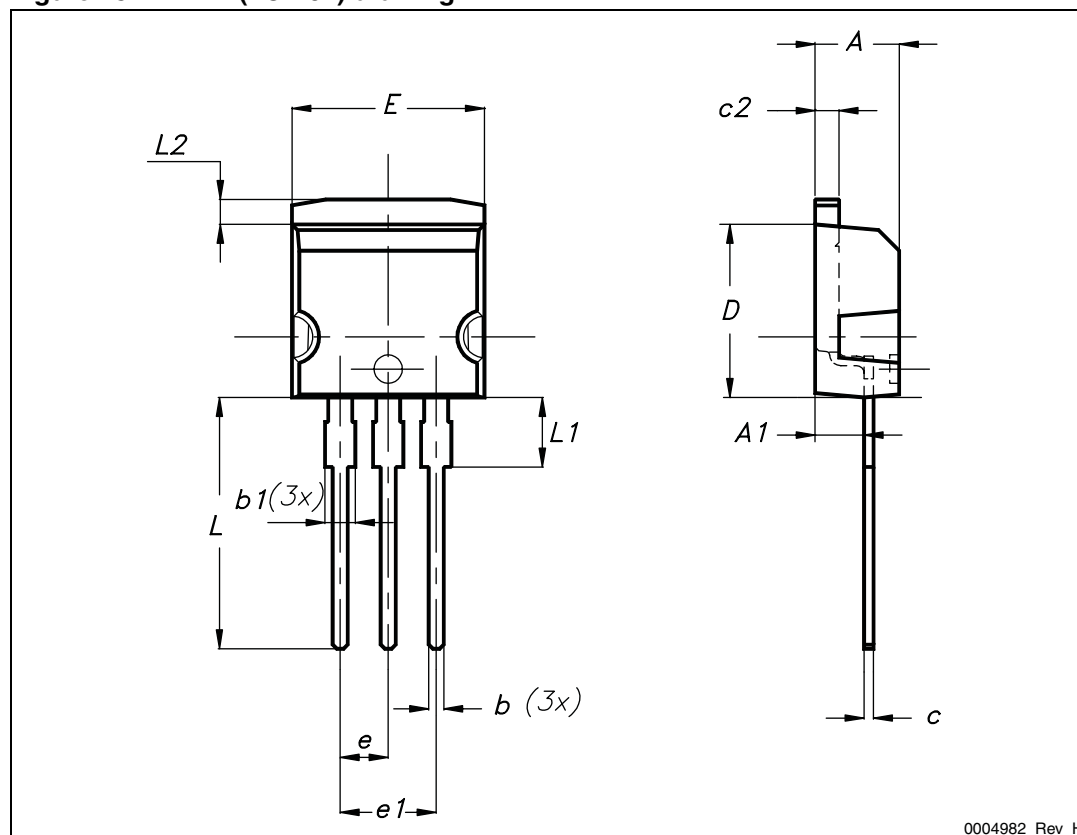
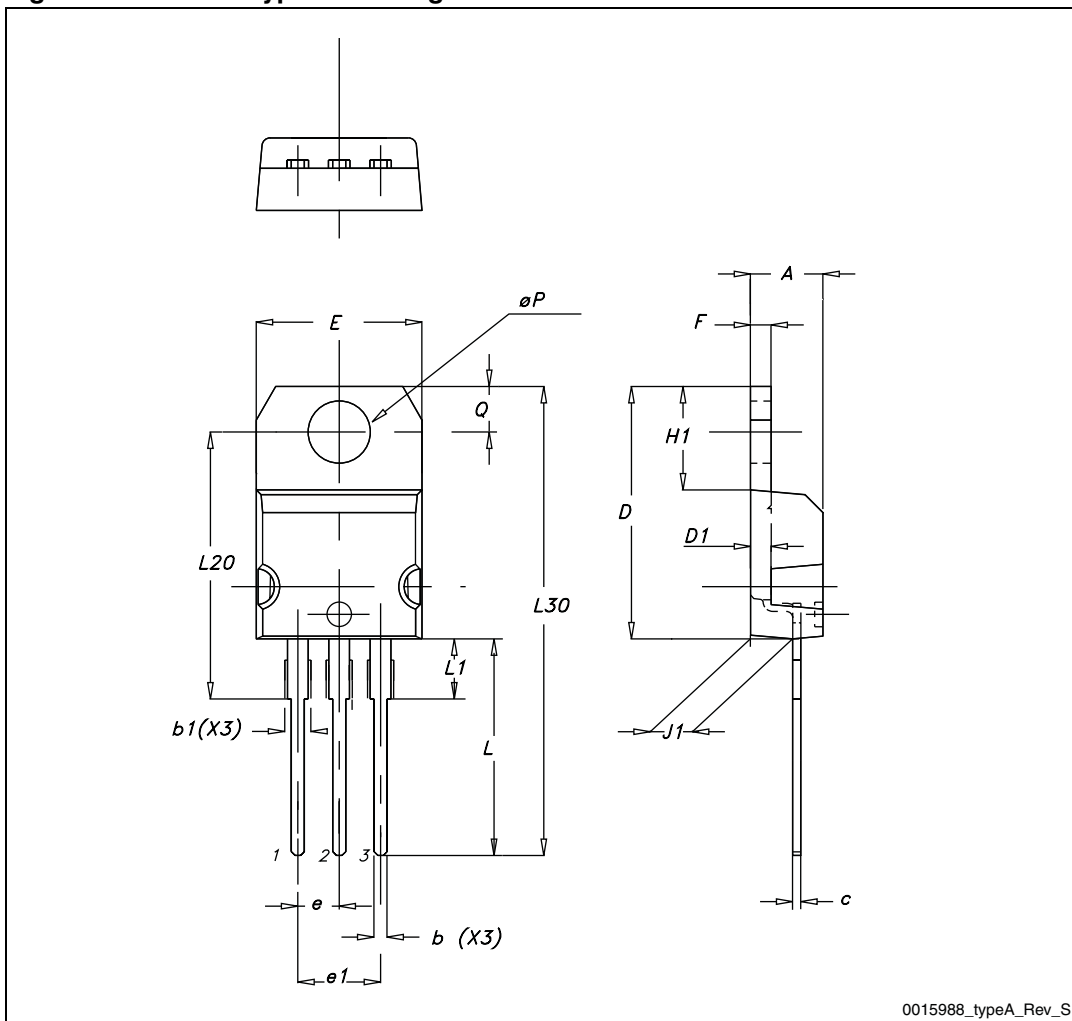
Figure 25. I<sup>2</sup>PAK (TO-262) drawing

Table 12. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 26. TO-220 type A drawing



0015988\_typeA\_Rev\_S

## 5 Revision history

**Table 13. Document revision history**

Date	Revision	Changes
08-Jun-2009	1	First release.
22-Jun-2009	2	Added new package, mechanical data: I <sup>2</sup> PAK
06-Aug-2012	3	Added package, mechanical data: I <sup>2</sup> PAKFP Updated <a href="#">Table 1: Device summary</a> , <a href="#">Table 2: Absolute maximum ratings</a> , <a href="#">Table 3: Thermal data</a> , <a href="#">Table 4: On /off states</a> . Minor text changes.
13-Sep-2012	4	Changed value in the title from 3.8 A to 8.4 A.



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